

CLC1007, CLC2007, CLC4007 Single, Dual, and Quad Low Cost,

High Speed RRO Amplifiers

General Description

The CLC1007 (single), CLC2007 (dual) and CLC4007(guad) are low cost, voltage feedback amplifiers. These amplifiers are designed to operate on +3V to +5V, or ±5V supplies. The input voltage range extends 300mV below the negative rail and 0.9V below the positive rail.

The CLC1007, CLC2007, and CLC4007 offer superior dynamic performance with a 260MHz small signal bandwidth and 220V/µs slew rate. The combination of low power, high output current drive, and rail-torail performance make these amplifiers well suited for battery-powered communication/computing systems.

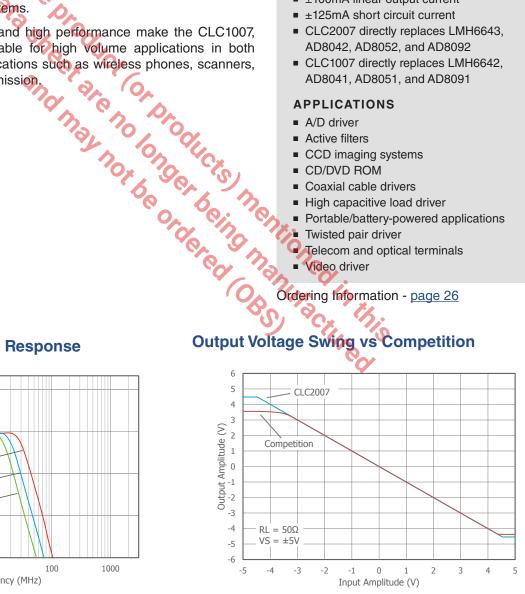
The combination of low cost and high performance make the CLC1007, CLC2007, and CLC4007 suitable for high volume applications in both consumer and industrial applications such as wireless phones, scanners, color copiers, and video transmission,

FEATURES

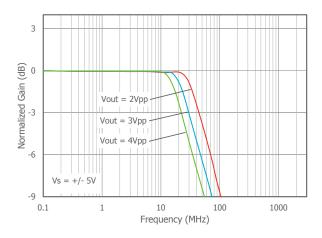
- 260MHz bandwidth
- Fully specified at +3V, +5V and ±5V supplies
- Output voltage range: • 0.03V to 4.95V; $V_S = +5$; $R_I = 2k\Omega$ Input voltage range:
- □ -0.3V to +4.1V; V_S = +5
- 220V/us slew rate
- 2.6mA supply current per amplifier
- ±100mA linear output current
- ±125mA short circuit current
- CLC2007 directly replaces LMH6643, AD8042, AD8052, and AD8092
- CLC1007 directly replaces LMH6642,

- Portable/battery-powered applications

Output Voltage Swing vs Competition



Large Signal Frequency Response



Absolute Maximum Ratings

Stresses beyond the limits listed below may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.

V _S 0\	/ to +14V
V _{IN} V _S - 0.5V to +	V _S +0.5V

Operating Conditions

Supply Voltage Range	2.7 to 12.6V
Operating Temperature Range	40°C to 125°C
Junction Temperature	150°C
Storage Temperature Range	65°C to 150°C
Lead Temperature (Soldering, 10s)	260°C

Package Thermal Resistance

θ _{JA} (TSC	0T23-5)215°C/W
θ _{JA} (SOI	C-8)150°C/W
θ _{JA} (MSC	DP-8) 200°C/W
	C-14) 90°C/W
θ _{JA} (TSS	OP-14)100°C/W
Package test boar	thermal resistance (θ_{JA}), JEDEC standard, multi-layer ds, still air.
ESD P	rotection
TSOT-5 (HBM)1kV
SOIC-8 (HBM)
TSOT-5 (CDM)2kV
SOIC-8 (CDM)2kV
ESD Rat Device M	ing for HBM (Human Body Model) and CDM (Charged lodel).
e ordering eq	C-8)

TSOT-5 (HBM)	1kV
SOIC-8 (HBM)	1kV
TSOT-5 (CDM)	2kV
боіс-в (СDM)	2kV
ESD Rating for HBM (Human Body Model) and CDM (Device Model).	(Charged

Electrical Characteristics at +3V

 T_A = 25°C, V_S = +3V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to $V_S/2;~G$ = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		90		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		245		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		16		MHz
BW_{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		55		MHz
D 0	Differential Oalia	DC-coupled Output		0.03		%
DG	Differential Gain	AC-coupled Output		0.04		%
55		DC-coupled Output		0.03		0
DP	Differential Phase	AC-coupled Output		0.06		0
Time Doma	in S		-1			
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step; (10% to 90%)		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 1V step		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		8		%
SR	Slew Rate	G = -1, 2V step		175		V/µs
Distortion/N	loise Response	Or Or				
THD	Total Harmonic Distortion	MHz, Vout = 1Vpp		75		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perform	ance	Do Do Ca				
V _{IO}	Input Offset Voltage			0.5		mV
d _{VIO}	Average Drift			5		μV/°C
I _B	Input Bias Current			1.4		μΑ
dl _B	Average Drift			2		nA/°C
I _{OS}	Input Offset Current			0.05		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$		92		dB
I _S	Supply Current	per channel	2.	2.6		mA
Input Chara	icteristics	<u> </u>	. %.			•
C _{IN}	Input Capacitance		S	0.5		pF
CMIR	Common Mode Input Range		60	-0.3 to 2.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0 to 1.5V		100		dB
Output Cha	racteristics		-1			
		R _L = 150Ω		0.3 to 2.75		V
V _{OUT} Output Swing		$R_L = 2k\Omega$		0.02 to 2.96		v
I _{OUT}	Output Current			±100		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S / 2$		±100		V
Vs	Power Supply Operating Range			2.7 to 12.6		v

Electrical Characteristics at +5V

 T_A = 25°C, V_S = +5V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to $V_S/2;~G$ = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency I	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		95		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		250		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		35		MHz
BW _{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		65		MHz
50	Differential Option	DC-coupled Output		0.03		%
DG	Differential Gain	AC-coupled Output		0.04		%
		DC-coupled Output		0.03		0
DP	Differential Phase	AC-coupled Output		0.06		0
Time Doma	in S. R		-			•
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	V _{OUT} = 2V step		25		ns
OS	Overshoot 7	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G=-1,4V step		220		V/µs
Distortion/N	loise Response	A (O ,				
THD	Total Harmonic Distortion	MHz, V _{OUT} = 2V _{pp}		-75		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perform	ance	no no Ca				•
V _{IO}	Input Offset Voltage		-7	0.5	7	mV
d _{VIO}	Average Drift			5		μV/°C
I _B	Input Bias Current		-2	1.4	2	μA
dl _B	Average Drift			2		nA/°C
I _{OS}	Input Offset Current		-0.75	0.05	0.75	μA
PSRR	Power Supply Rejection Ratio	DC C	80	102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$	80	92		dB
I _S	Supply Current	per channel	2.	2.6	4	mA
Input Chara	acteristics		· %.			•
C _{IN}	Input Capacitance		S	0.5		pF
CMIR	Common Mode Input Range		80	-0.3 to 4.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = 0 to 3.5V	75	100		dB
Output Cha	racteristics		1			
	O to to to int	R _L = 150Ω	0.35	0.1 to 4.9	4.65	V
V _{OUT}	Output Swing	$R_L = 2k\Omega$		0.03 to 4.95		V
I _{OUT}	Output Current			±100		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S / 2$		±125		V
V _S	Power Supply Operating Range			2.7 to 12.6		v

Electrical Characteristics at ±5V

 T_A = 25°C, V_S = ±5V, R_f = 1.5k $\Omega,~R_L$ = 2k Ω to GND; G = 2; unless otherwise noted.

Symbol	Parameter	Conditions	Min	Тур	Max	Units
Frequency I	Domain Response					
GBWP	-3dB Gain Bandwidth Product	$G = +11, V_{OUT} = 0.2V_{pp}$		90		MHz
UGBW	Unity Gain Bandwidth	$V_{OUT} = 0.2V_{pp}, R_F = 0$		260		MHz
BW _{SS}	-3dB Bandwidth	$V_{OUT} = 0.2V_{pp}$		85		MHz
f _{0.1dB}	0.1dB Gain Flatness	$V_{OUT} = 0.2V_{pp}, R_L = 150\Omega$		22		MHz
BW _{LS}	Large Signal Bandwidth	$V_{OUT} = 2V_{pp}$		65		MHz
D 0	Differential Onio	DC-coupled Output		0.03		%
DG	Differential Gain	AC-coupled Output		0.04		%
55		DC-coupled Output		0.03		0
DP	Differential Phase	AC-coupled Output		0.06		0
Time Doma	in O		-			
t _R , t _F	Rise and Fall Time	V _{OUT} = 0.2V step		5		ns
t _S	Settling Time to 0.1%	$V_{OUT} = 2V$ step, $R_L = 100\Omega$		25		ns
OS	Overshoot	V _{OUT} = 0.2V step		5		%
SR	Slew Rate	G = -1, 5V step		225		V/µs
Distortion/N	loise Response					
THD	Total Harmonic Distortion	MHz, V _{OUT} = 2V _{pp}		76		dBc
e _n	Input Voltage Noise	>50kHz		16		nV/√Hz
X _{TALK}	Crosstalk	f = 5MHz		58		dB
DC Perform	ance	1 h C				
V _{IO}	Input Offset Voltage			0.5		mV
d _{VIO}	Average Drift			5		μV/°C
I _B	Input Bias Current			1.3		μΑ
dl _B	Average Drift			2		nA/°C
I _{OS}	Input Offset Current			0.04		μA
PSRR	Power Supply Rejection Ratio	DC		102		dB
A _{OL}	Open Loop Gain	$R_L = 2k\Omega$		92		dB
I _S	Supply Current	per channel	2.	2.6		mA
Input Chara	cteristics	S. S.	· %.			
C _{IN}	Input Capacitance		S	0.5		pF
CMIR	Common Mode Input Range		80	-5.3 to 4.1		V
CMRR	Common Mode Rejection Ratio	DC, V _{CM} = -5 to 3.5V		100		dB
Output Cha	racteristics		1			
		R _L = 150Ω		-4.8 to 4.8		V
V _{OUT}	Output Swing	$R_L = 2k\Omega$		-4.95 to 4.93		V
IOUT	Output Current			±100		mA
I _{SC}	Short Circuit Current	$V_{OUT} = V_S / 2$		±100		V
.30				2.7 to		v

CLC1007 Pin Configurations TSOT-5

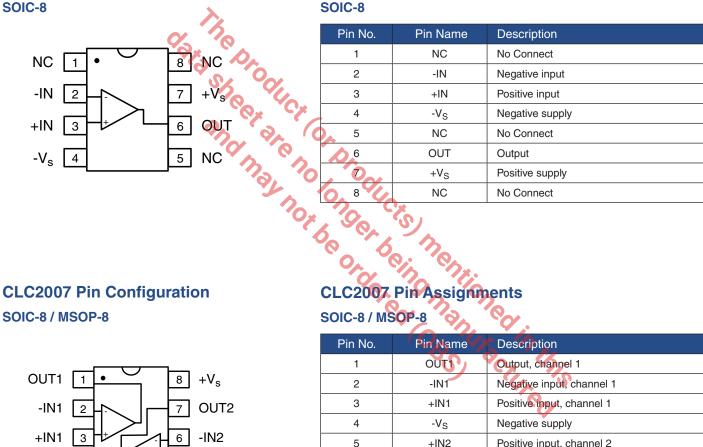
OUT 5 $+V_{s}$ 1 -Vs 2 +IN 3 4 -IN

CLC1007 Pin Assignments

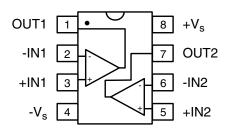
TSOT-5

Pin No.	Pin Name	Description
1	OUT	Output
2	-V _S	Negative supply
3	+IN	Positive input
4	-IN	Negative input
5	+V _S	Positive supply

SOIC-8

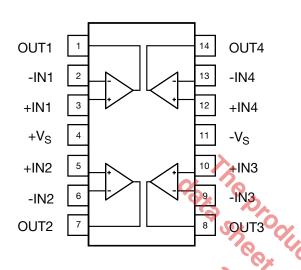


CLC2007 Pin Configuration SOIC-8 / MSOP-8



Pin No.	Pin Name	Description
1	OUT	Output, channel 1
2	-IN1	Negative input, channel 1
3	+IN1	Positive input, channel 1
4	-V _S	Negative supply
5	+IN2	Positive input, channel 2
6	-IN2	Negative input, channel 2
7	OUT2	Output, channel 2
8	+V _S	Positive supply

CLC4007 Pin Configuration SOIC-14 / TSSOP-14



CLC4007 Pin Assignments

SOIC-14 / TSSOP-14

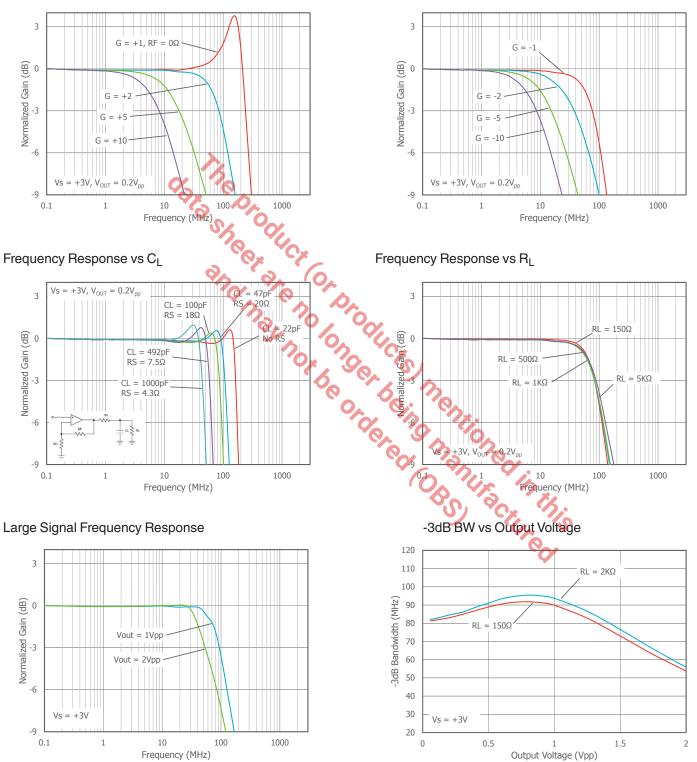
abannal 1	Pin Name	Pin No.	
t, channel 1	OUT1	1	
ve input, channel 1	-IN1	2	
e input, channel 1	+IN1	3	OUT4
e supply	+V _S	4	-IN4
e input, channel 2	+IN2	5	
ve input, channel 2	-IN2	6	+IN4
t, channel 2	OUT2	7	-V _S
t, channel 3	OUT3	8	-
ve input, channel 3	-IN3	9	+IN3
e input, channel 3	+IN3	10	-IN3
ve supply	-V _S	11	Dr
e input, channel 4	+IN4	12	OUT3
ve input, channel 4	-IN4	13	
, channel 4	OUT4	14	
This	ing manuficity of the second s	nger b order	

Typical Performance Characteristics at +3V

 $T_A = 25^{\circ}C$, $V_S = +3V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

Non-Inverting Frequency Response

Inverting Frequency Response

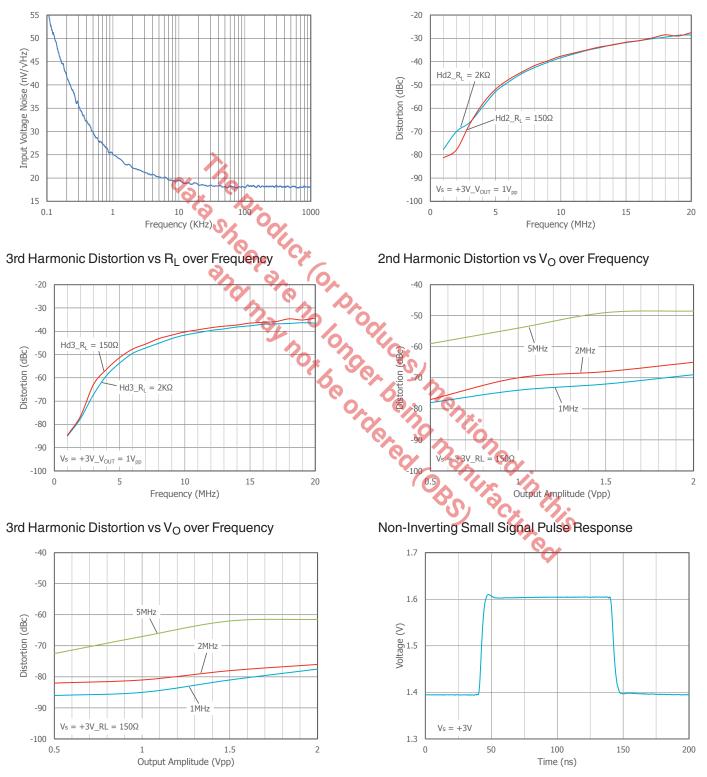


Typical Performance Characteristics at +3V

 T_A = 25°C, V_S = +3V, R_L = 2k Ω to $V_S/2,~G$ = +2, R_F = 1.5k $\Omega;$ unless otherwise noted.

Input Voltage Noise vs Frequency

2nd Harmonic Distortion vs RL over Frequency

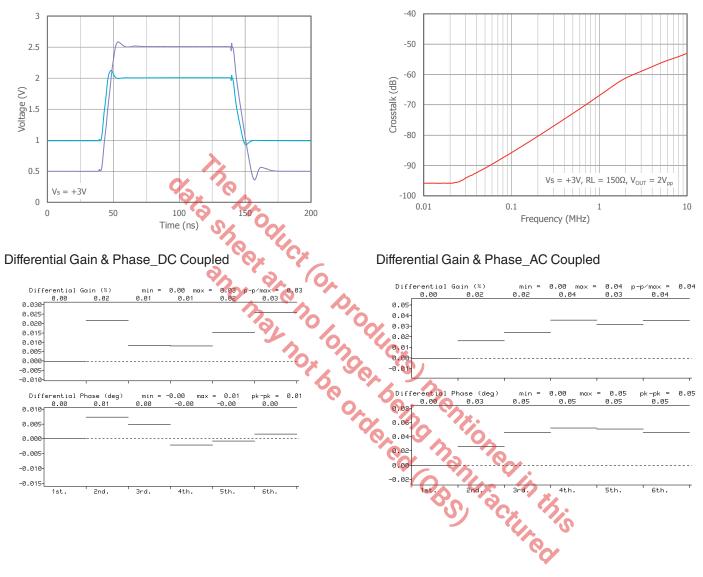


Typical Performance Characteristics at +3V

 $T_A = 25^{\circ}C$, $V_S = +3V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

Non-Inverting Large Signal Pulse Response

Crosstalk vs Frequency (CLC2007)

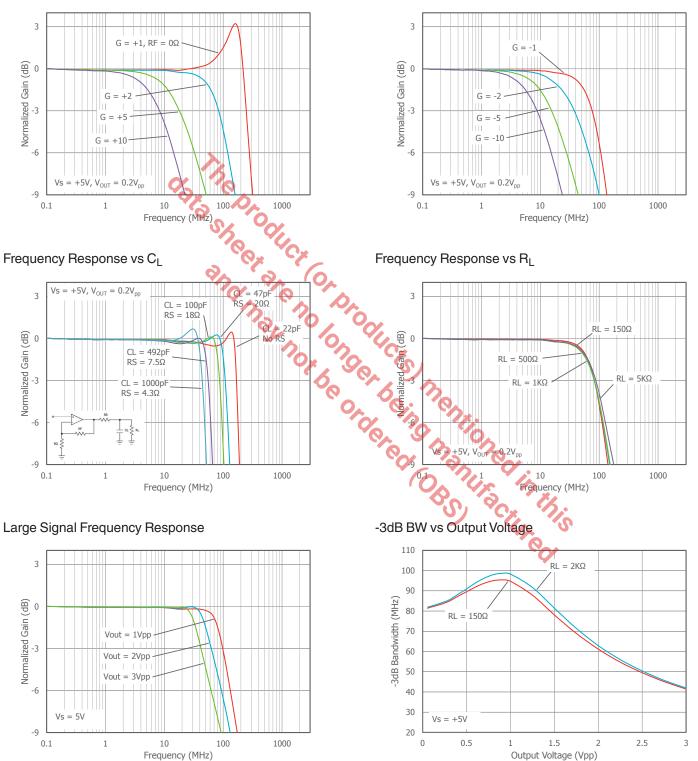


Typical Performance Characteristics at +5V

 $T_A = 25^{\circ}C$, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

Non-Inverting Frequency Response

Inverting Frequency Response

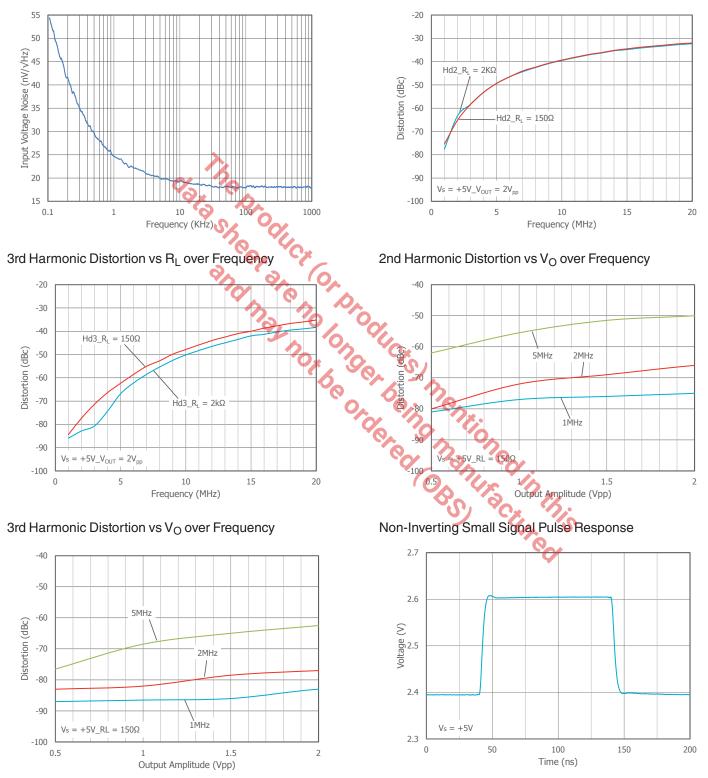


Typical Performance Characteristics at +5V

 T_A = 25°C, V_S = +5V, R_L = 2k Ω to $V_S/2,~G$ = +2, R_F = 1.5k $\Omega;$ unless otherwise noted.

Input Voltage Noise vs Frequency

2nd Harmonic Distortion vs RL over Frequency

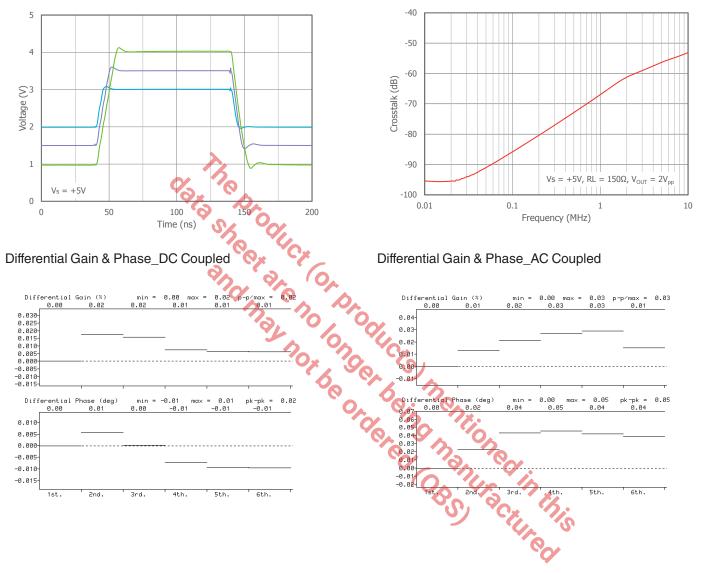


Typical Performance Characteristics at +5V

 $T_A = 25^{\circ}C$, $V_S = +5V$, $R_L = 2k\Omega$ to $V_S/2$, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

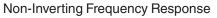
Non-Inverting Large Signal Pulse Response

Crosstalk vs Frequency (CLC2007)

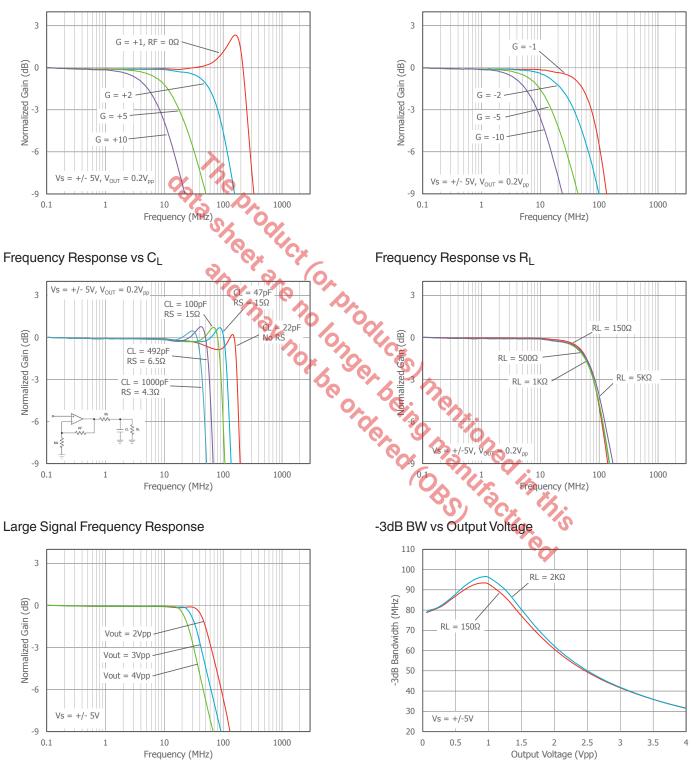


Typical Performance Characteristics at ±5V

 $T_A = 25^{\circ}C$, $V_S = \pm 5V$, $R_L = 2k\Omega$ to GND, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.



Inverting Frequency Response

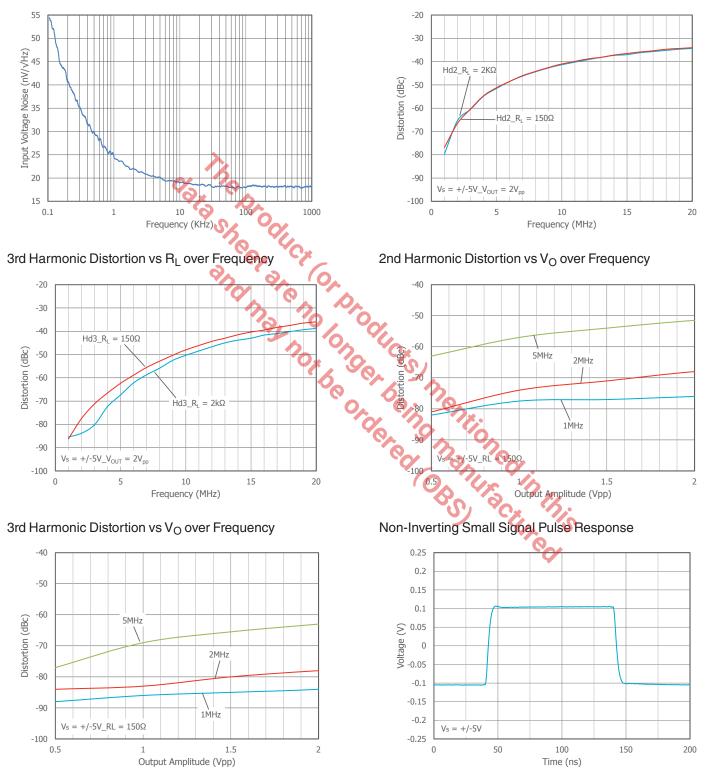


Typical Performance Characteristics at ±5V

 $T_A = 25^{\circ}C$, $V_S = \pm 5V$, $R_L = 2k\Omega$ to GND, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

Input Voltage Noise vs Frequency

2nd Harmonic Distortion vs RL over Frequency

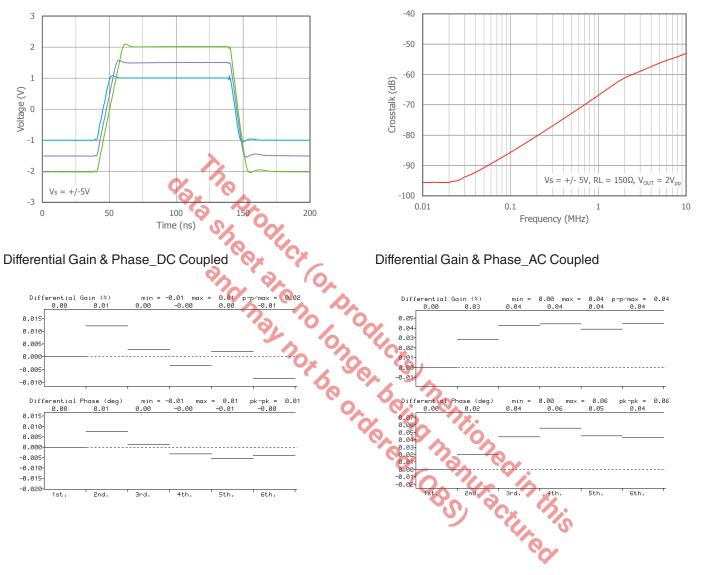


Typical Performance Characteristics at ±5V

 $T_A = 25^{\circ}C$, $V_S = \pm 5V$, $R_L = 2k\Omega$ to GND, G = +2, $R_F = 1.5k\Omega$; unless otherwise noted.

Non-Inverting Large Signal Pulse Response

Crosstalk vs Frequency (CLC2007)



Application Information

General Description

The CLC1007, CLC2007, and CLC4007 are single supply, general purpose, voltage-feedback amplifiers fabricated on a complementary bipolar process using a patent pending topography. They feature a rail-to-rail output stage and is unity gain stable. Both gain bandwidth and slew rate are insensitive to temperature.

The common mode input range extends to 300mV below ground and to 0.9V below Vs. Exceeding these values will not cause phase reversal. However, if the input voltage exceeds the rails by more than 0.5V, the input ESD devices will begin to conduct. The output will stay at the rail during this overdrive condition.

The design is short circuit protected and offers "soft" saturation protection that improves recovery time.

Figures 1, 2, and 3 illustrate typical circuit configurations for non-inverting, inverting, and unity gain topologies for dual supply applications. They show the recommended bypass capacitor values and overall closed loop gain equations. Figure 4 shows the typical non-inverting gain circuit for single supply applications.

6.8µF

0.1µF

0.1µF

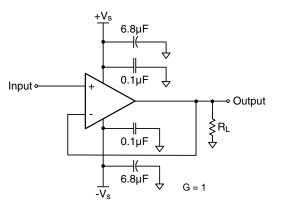
6.8µF

R

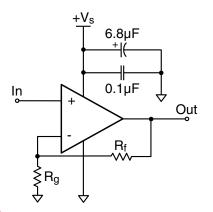
Output

≶R∟

 $G = 1 + (R_f/R_a)$







ingle support

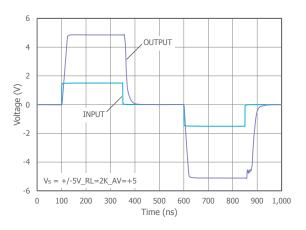
Image: Support

Figure 4: Single Supply Non-Inverting Gain Circuit

Output

Overdrive Recovery

Image: Supply Recovery For an amplifier, an overdrive condition occurs when the output and/or input ranges are exceeded. The recovery time varies based on whether the input or output is overdriven and by how much the ranges are exceeded. The CLC1007, CLC2007, and CLC4007 will typically recover in less than 20ns from an overdrive condition. Figure 5 shows the CLC2007 in an overdriven condition.



ŞRg ↓ -V. Figure 1: Typical Non-Inverting Gain Circuit

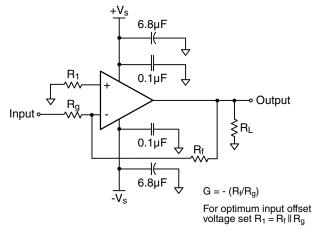




Figure 5: Overdrive Recovery

Input

Power Dissipation

Power dissipation should not be a factor when operating under the stated $2k\Omega$ load condition. However, applications with low impedance, DC coupled loads should be analyzed to ensure that maximum allowed junction temperature is not exceeded. Guidelines listed below can be used to verify that the particular application will not cause the device to operate beyond it's intended operating range.

Maximum power levels are set by the absolute maximum junction rating of 170°C. To calculate the junction temperature, the package thermal resistance value Theta_{JA} (θ_{JA}) is used along with the total die power dissipation.

$$T_{Junction} = T_{Ambient} + (\theta_{JA} \times P_D)$$

Where T_{Ambient} is the temperature of the working environment.

In order to determine P_D, the power dissipated in the load needs to be subtracted from the total power delivered by the supplies.

$$P_D = P_{supply} - P_{loa}$$

Supply power is calculated by the standard power equation.

$$P_{supply} = V_{supply} \times I_{RMSsupply}$$

$$V_{supply} = V_{S+} - V_{S-}$$

Power delivered to a purely resistive load is:

$$P_{load} = ((V_{load})_{RMS^2})/Rload_{eff}$$

The effective load resistor ($Rload_{eff}$) will need to include the effect of the feedback network. For instance,

Rload_{eff} in Figure 3 would be calculated as:

$$R_L \parallel (R_f + R_g)$$

These measurements are basic and are relatively easy to perform with standard lab equipment. For design purposes however, prior knowledge of actual signal levels and load impedance is needed to determine the dissipated power. Here, P_D can be found from

$$P_D = P_{Quiescent} + P_{Dynamic} - P_{load}$$

Quiescent power can be derived from the specified I_S values along with known supply voltage, V_{supply} . Load power can be calculated as above with the desired signal amplitudes using:

$$(V_{load})_{RMS} = V_{peak} / \sqrt{2}$$

 $(I_{load})_{RMS} = (V_{load})_{RMS} / Rload_{eff}$

The dynamic power is focused primarily within the output stage driving the load. This value can be calculated as:

 $P_{Dynamic} = (V_{S+} - V_{load})_{RMS} \times (I_{load})_{RMS}$

Assuming the load is referenced in the middle of the power rails or $V_{supply}/2$.

The CLC1007 is short circuit protected. However, this may not guarantee that the maximum junction temperature (+150°C) is not exceeded under all conditions. Figure 6 shows the maximum safe power dissipation in the package vs. the ambient temperature for the packages available.

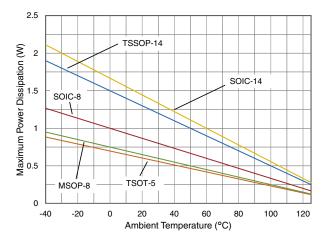


Figure 6. Maximum Power Derating

Driving Capacitive Loads

Increased phase delay at the output due to capacitive loading can cause ringing, peaking in the frequency response, and possible unstable behavior. Use a series resistance, R_S, between the amplifier and the load to help improve stability and settling performance. Refer to Figure 7.

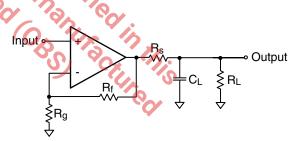


Figure 7. Addition of R_S for Driving Capacitive Loads

Table 1 provides the recommended R_S for various capacitive loads. The recommended R_S values result in approximately <1dB peaking in the frequency response.

C _L (pF)	R _S (Ω)	-3dB BW (MHz)
22pF	0	118
47pF	15	112
100pF	15	91
492pF	6.5	59

Table 1: Recommended R_S vs. C_L

For a given load capacitance, adjust R_S to optimize the tradeoff between settling time and bandwidth. In general, reducing R_S will increase bandwidth at the expense of additional overshoot and ringing.

Layout Considerations

General layout and supply bypassing play major roles in high frequency performance. Exar has evaluation boards to use as a guide for high frequency layout and as an aid in device testing and characterization. Follow the steps below as a basis for high frequency layout:

- Include 6.8µF and 0.1µF ceramic capacitors for power supply decoupling
- Place the 6.8µF capacitor within 0.75 inches of the power pin
- Place the 0.1µF capacitor within 0.1 inches of the power pin
- Remove the ground plane under and around the part, especially near the input and output pins to reduce parasitic capacitance
- Minimize all trace lengths to reduce series inductances

Refer to the evaluation board layouts below for more information.

Evaluation Board Information

The following evaluation boards are available to aid in the testing and layout of these devices:

Products
CLC1007 in TSOT
CLC1007 in SOIC
CLC2007 in SOIC
CLC2007 in MSOP
CLC4007 in SOIC
CLC4007 in TSSOP

Evaluation Board Schematics

Evaluation board schematics and layouts are shown in Figures 8-20. These evaluation boards are built for dualsupply operation. Follow these steps to use the board in a single-supply application:

- 1. Short -V_S to ground.
- 2. Use C3 and C4, if the -V_S pin of the amplifier is not directly connected to the ground plane.

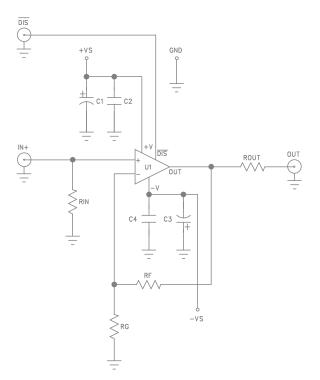


Figure 8. CEB002 & CEB003 Schematic

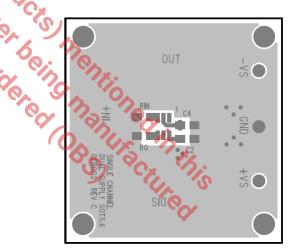


Figure 9. CEB002 Top View

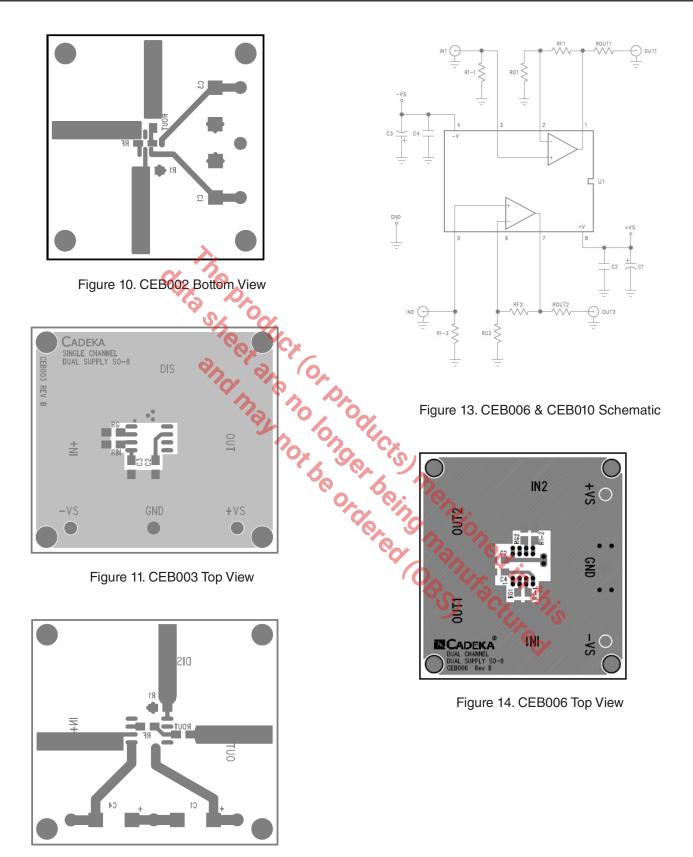


Figure 12. CEB003 Bottom View

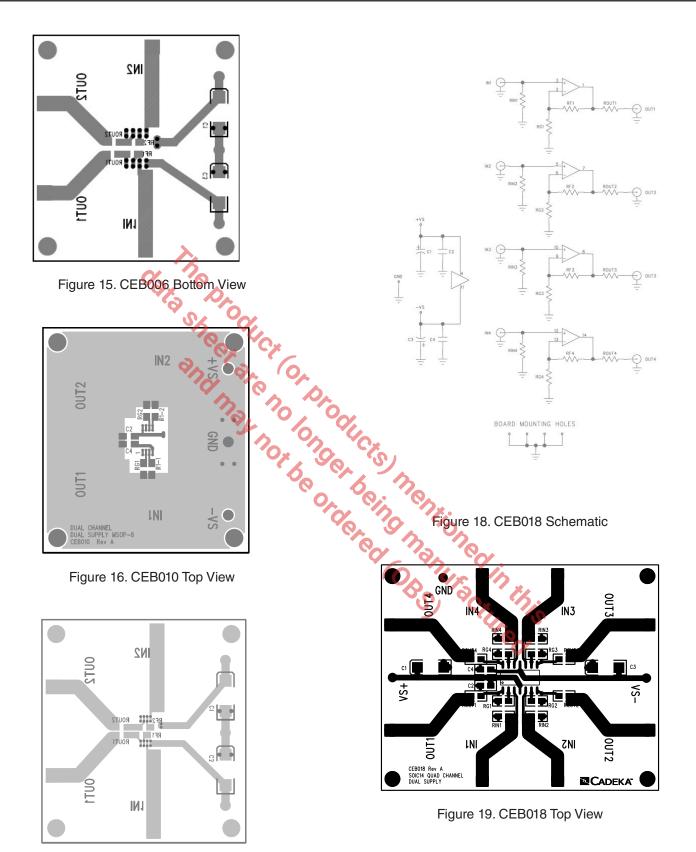
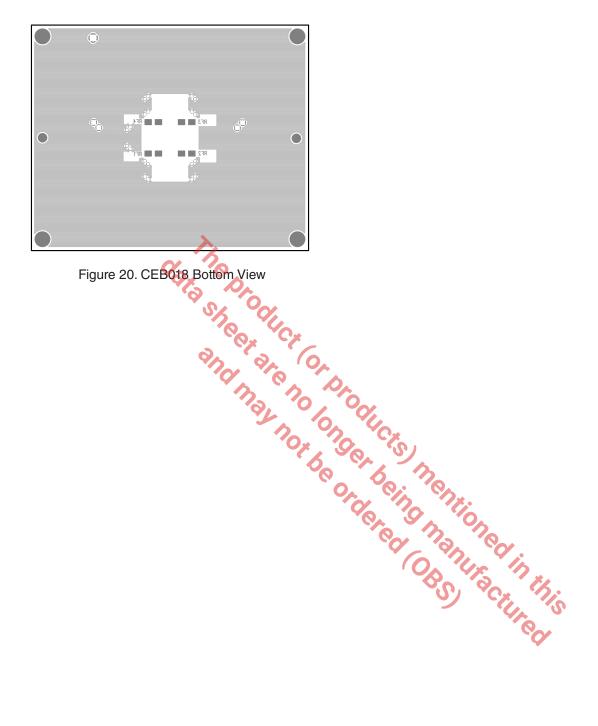
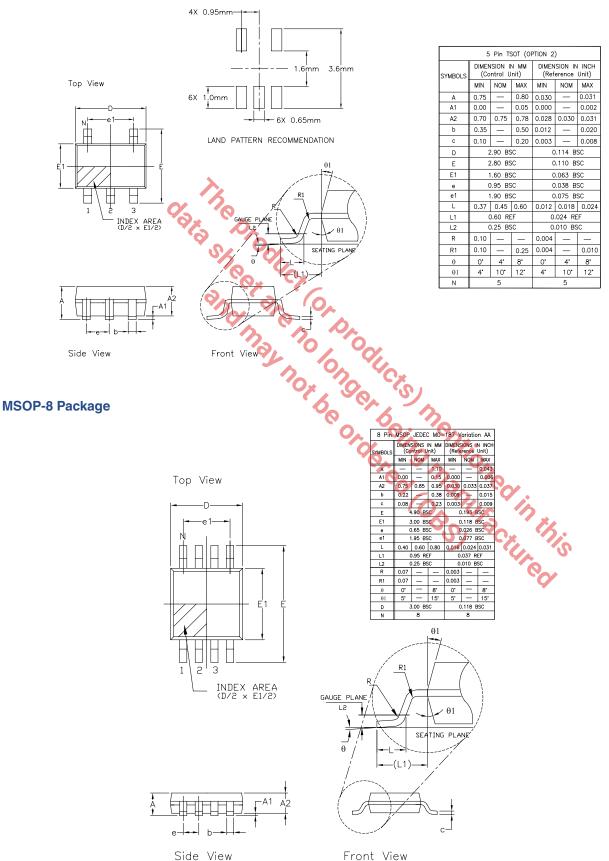


Figure 17. CEB010 Bottom View



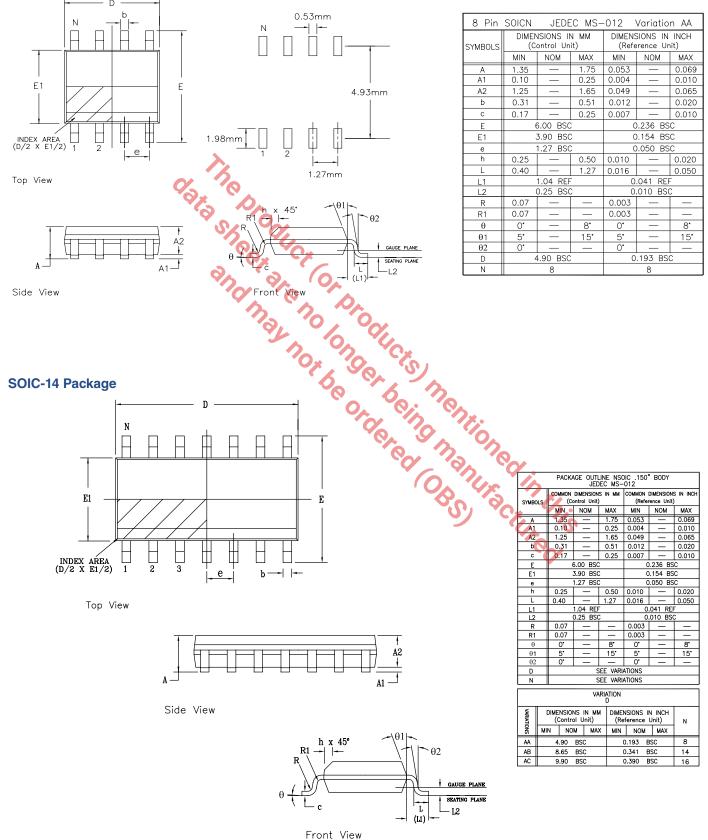
Mechanical Dimensions

TSOT-5 Package

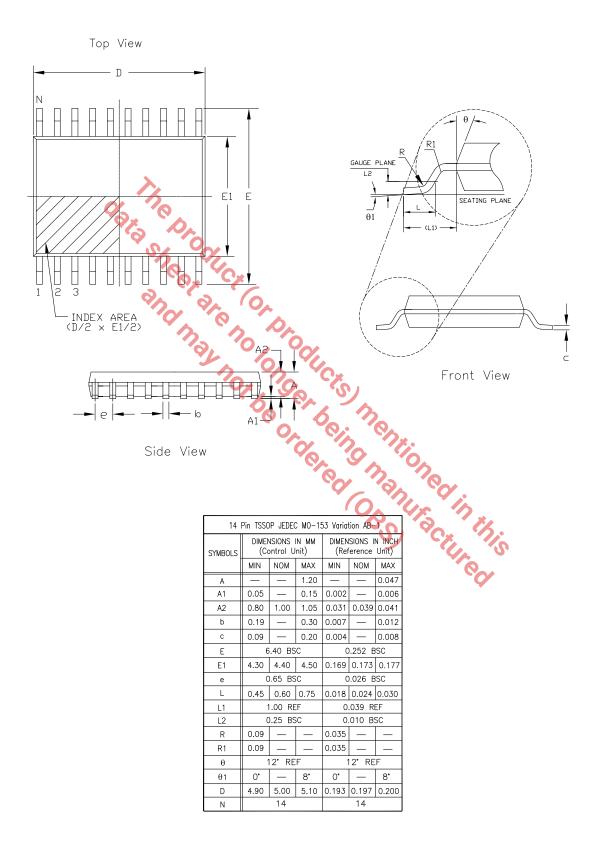


SOIC-8 Package

RECOMMENDED PCB LAND PATTERN



TSSOP-14 Package



Ordering Information

Part Number	Package	Green	Operating Temperature Range	Packaging
CLC1007 Ordering Information	l		II	
CLC1007IST5X	TSOT-5	Yes	-40°C to +125°C	Tape & Reel
CLC1007IST5MTR	TSOT-5	Yes	-40°C to +125°C	Mini Tape & Reel
CLC1007IST5EVB	Evaluation Board	N/A	N/A	N/A
CLC1007ISO8X	SOIC-8	Yes	-40°C to +125°C	Tape & Reel
CLC1007ISO8MTR	SOIC-8	Yes	-40°C to +125°C	Mini Tape & Reel
CLC1007ISO8EVB	Evaluation Board	N/A	N/A	N/A
CLC2007 Ordering Information		·	· · · · · · · · · · · · · · · · · · ·	
CLC2007ISO8X	SOIC-8	Yes	-40°C to +125°C	Tape & Reel
CLC2007ISO8MTR	SOIC-8	Yes	-40°C to +125°C	Mini Tape & Reel
CLC2007ISO8EVB	Evaluation Board	N/A	N/A	N/A
CLC2007IMP8X	MSOP-8	Yes	-40°C to +125°C	Tape & Reel
CLC2007IMP8MTR	MSOP-8	Yes	-40°C to +125°C	Mini Tape & Reel
CLC2007IMP8EVB	Evaluation Board	N/A	N/A	N/A
CLC4007 Ordering Information	97.94	0		
CLC4007ITP14X	TSSOP-14	Yes	-40°C to +125°C	Tape & Reel
CLC4007ITP14MTR	TSSOP-14	Yes O	-40°C to +125°C	Mini Tape & Reel
CLC4007ITP14EVB	Evaluation Board	N/A	N/A	N/A
CLC4007ISO14X	SOIC-14	Yes	-40°C to +125°C	Tape & Reel
CLC4007ISO14MTR	SOIC-14	Yes	-40°C to +125°C	Mini Tape & Reel
CLC4007ISO14EVB	Evaluation Board	N/A	N/A	N/A

Moisture sensitivity level for all parts is MSL-1.

A C to +12. A C N/A TORRES OR THIS C B C TURRED IN THIS

Revision History

Revision	Date	Description
1D (ECN 1451-07)	December 2014	Reformat into Exar data sheet template. Updated ordering information table to include MTR and EVB part numbers. Increased "I" temperature range from +85 to +125°C. Removed "A" temp grade parts, since "I" is now equivalent. Updated thermal resistance numbers and package outline drawings.

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